

Silicon NPN Power Transistors

2SD1344

DESCRIPTION

- With TO-3 package
- High voltage
- Built-in damper diode

APPLICATIONS

- For color TV horizontal deflection output applications

PINNING(see fig.2)

PIN	DESCRIPTION
1	Base
2	Emitter
3	Collector

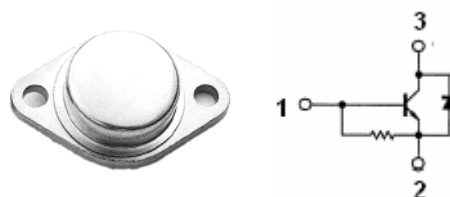


Fig.1 simplified outline (TO-3) and symbol

Absolute maximum ratings($T_a = \square$)

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
V_{CBO}	Collector-base voltage	Open emitter	1500	V
V_{CEO}	Collector-emitter voltage	Open base	600	V
V_{EBO}	Emitter-base voltage	Open collector	5	V
I_C	Collector current		6	A
P_T	Total power dissipation	$T_C = 25 \square$	50	W
T_j	Junction temperature		150	$\square$
T_{stg}	Storage temperature		-40~150	$\square$

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CHARACTERISTICS

Tj=25°C unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
$V_{CEQ(SUS)}$	Collector-emitter sustaining voltage	$I_C=100\text{mA}; I_B=0$	600			V
$V_{(BR)EBO}$	Emitter-base breakdown voltage	$I_E=200\text{mA}; I_C=0$	5			V
V_{CEsat}	Collector-emitter saturation voltage	$I_C=4\text{A}; I_B=0.8\text{A}$			5.0	V
V_{BEsat}	Base-emitter saturation voltage	$I_C=4\text{A}; I_B=0.8\text{A}$			1.5	V
I_{CBO}	Collector cut-off current	$V_{CB}=800\text{V}; I_E=0$			10	μA
h_{FE-1}	DC current gain	$I_C=0.5\text{A}; V_{CE}=5\text{V}$	10			
h_{FE-2}	DC current gain	$I_C=3\text{A}; V_{CE}=5\text{V}$	5			
V_F	Diode forward voltage	$I_F=4\text{A}$			2.0	V

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PACKAGE OUTLINE

